



Low beam energy Ion Implantation

1. Note

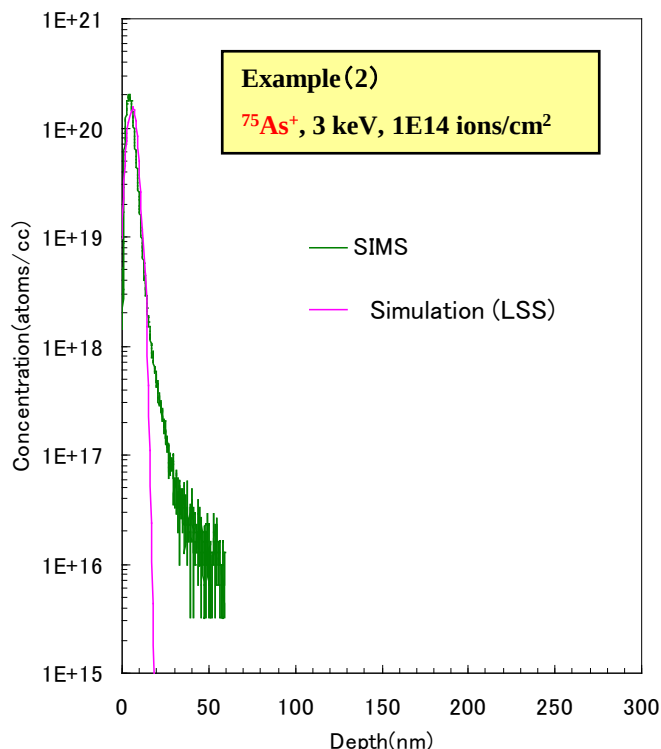
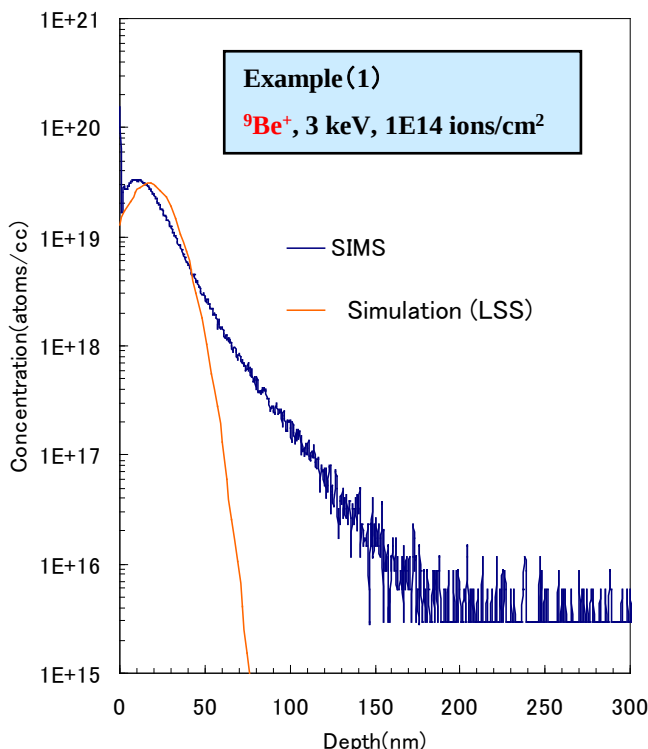
Ion Implanter of TRC in Japan can produce lower beam energy than 10 keV in order to meet customer need for shallow layer implantation.

※) Almost all ion specie is OK, to the extent of the implanter of TRC in Japan.

※) Less than 10 keV implantation is out of certification because it is out from the machine specification.

2. Features

- Machine: Middle-currenty Ion Implanter (ULVAC IMX3500RS)
- Size: Max 6 inch
- Energy: Min 3 keV
- Dose: $5.0 \times 10^{11} \sim 1.0 \times 10^{17}$ ions/cm²



※) Molecular ions such as H₂, BF₂, P₂ and H₂O can be adopted to substantive lower energy implant.